

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3434 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Super low on-state resistance:
 $R_{DS(on)1} = 20\text{ m}\Omega$ MAX. ($V_{GS} = 10\text{ V}$, $I_D = 24\text{ A}$)
- ★ $R_{DS(on)2} = 31\text{ m}\Omega$ MAX. ($V_{GS} = 4.0\text{ V}$, $I_D = 24\text{ A}$)
- Low C_{iss} : $C_{iss} = 2100\text{ pF}$ TYP.
- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 48	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 192	A
★ Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_T	56	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.5	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$
★ Single Avalanche Current ^{Note2}	I_{AS}	28	A
★ Single Avalanche Energy ^{Note2}	E_{AS}	78	mJ

Notes 1. $PW \leq 10\text{ }\mu\text{s}$, Duty cycle $\leq 1\%$

2. Starting $T_{ch} = 25\text{ }^\circ\text{C}$, $R_G = 25\text{ }\Omega$, $V_{GS} = 20\text{ V} \rightarrow 0\text{ V}$

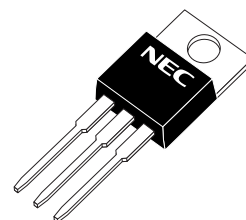
THERMAL RESISTANCE

★ Channel to Case	$R_{th(ch-C)}$	2.23	$^\circ\text{C/W}$
Channel to Ambient	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$

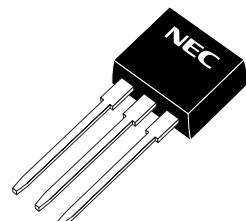
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3434	TO-220AB
2SK3434-S	TO-262
2SK3434-Z	TO-220SMD

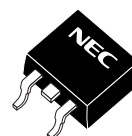
(TO-220AB)



(TO-262)



(TO-220SMD)

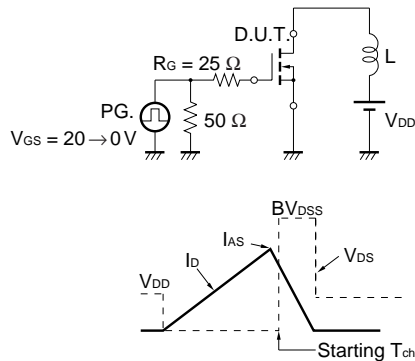


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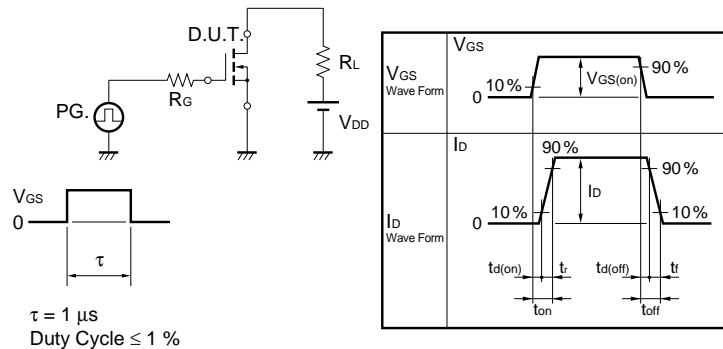
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
★	Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 24 A		16	20	mΩ
		R _{DS(on)2}	V _{GS} = 4.0 V, I _D = 24 A		22	31	mΩ
	Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
★	Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 24 A	13	27		S
	Drain Leakage Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			10	μA
	Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
★	Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		2100		pF
	Output Capacitance	C _{oss}			340		pF
	Reverse Transfer Capacitance	C _{rss}			170		pF
★	Turn-on Delay Time	t _{d(on)}	I _D = 24 A, V _{GS(on)} = 10 V, V _{DD} = 30 V, R _G = 10 Ω		40		ns
★	Rise Time	t _r			400		ns
★	Turn-off Delay Time	t _{d(off)}			120		ns
★	Fall Time	t _f			160		ns
★	Total Gate Charge	Q _G	I _D = 48 A, V _{DD} = 48 V, V _{GS} = 10 V		40		nC
	Gate to Source Charge	Q _{GS}			7		nC
	Gate to Drain Charge	Q _{GD}			11		nC
	Body Diode Forward Voltage	V _{F(S-D)}	I _F = 48 A, V _{GS} = 0 V		1.0		V
★	Reverse Recovery Time	t _{rr}	I _F = 48 A, V _{GS} = 0 V,		43		ns
★	Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		61		nC

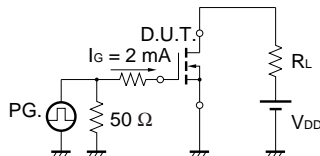
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

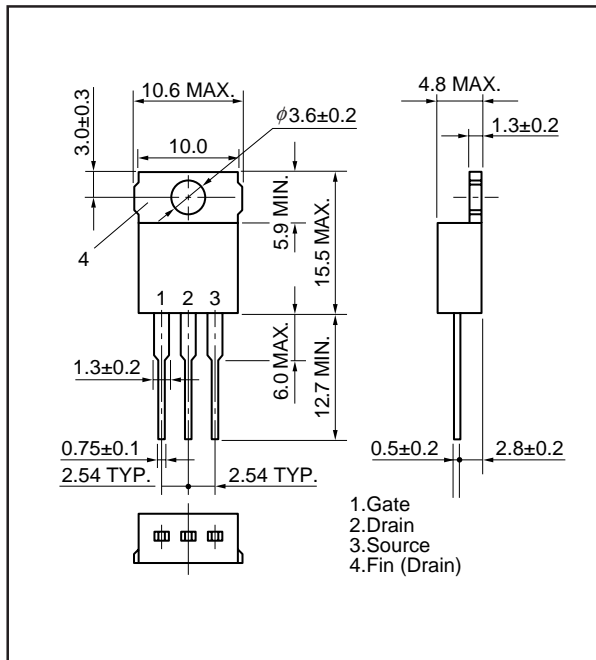


TEST CIRCUIT 3 GATE CHARGE

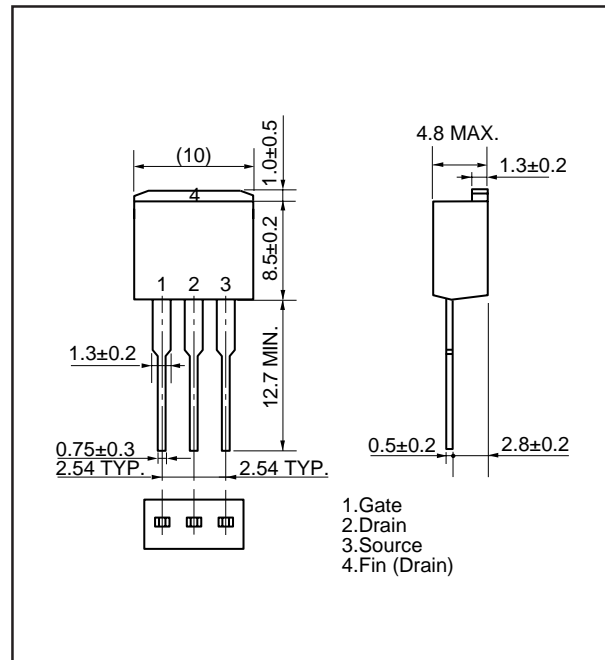


PACKAGE DRAWINGS (Unit: mm)

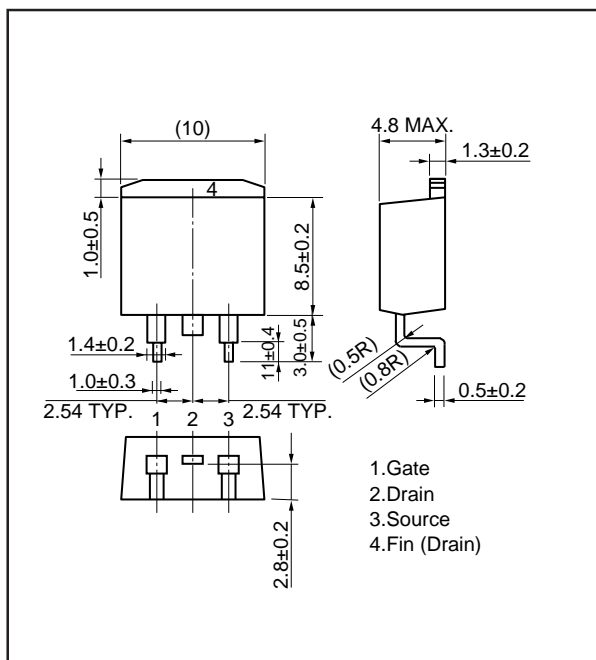
1) TO-220AB (MP-25)



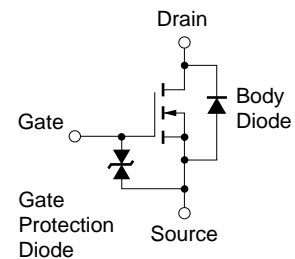
2) TO-262 (MP-25 Fin Cut)



3) TO-220SMD (MP-25Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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